

ECE 456 - Problem Set 1

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Well done, David and
Phillip!

- Alan

Q1:
15/15

Question 1

(a)

Beginning with the following two equations:

$$N = \int_{-\infty}^{\infty} \frac{\gamma_1 f_1(E) + \gamma_2 f_2(E)}{\gamma_1 + \gamma_2} D(E - U) dE, \quad (1)$$

$$I = \frac{q}{\hbar} \frac{\gamma_1 \gamma_2}{\gamma_1 + \gamma_2} \int_{-\infty}^{\infty} [f_1(E) - f_2(E)] D(E - U) dE, \quad (2)$$

and changing the variable of integration to $E' = E - U$:

$$N = \int_{-\infty}^{\infty} \frac{\gamma_1 f_1(E' + U) + \gamma_2 f_2(E' + U)}{\gamma_1 + \gamma_2} D(E') dE',$$

$$I = \frac{q}{\hbar} \frac{\gamma_1 \gamma_2}{\gamma_1 + \gamma_2} \int_{-\infty}^{\infty} [f_1(E' + U) - f_2(E' + U)] D(E') dE'.$$

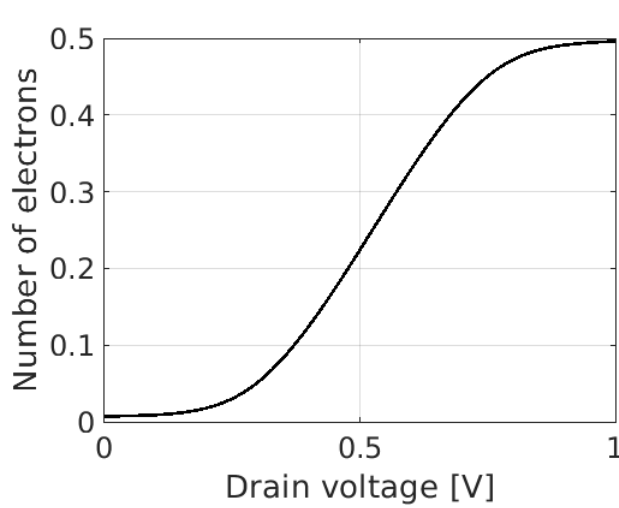
Replacing $E' \rightarrow E$, we obtain equations 3 and 4.

$$N = \int_{-\infty}^{\infty} \frac{\gamma_1 f_1(E + U) + \gamma_2 f_2(E + U)}{\gamma_1 + \gamma_2} D(E) dE, \quad (3)$$

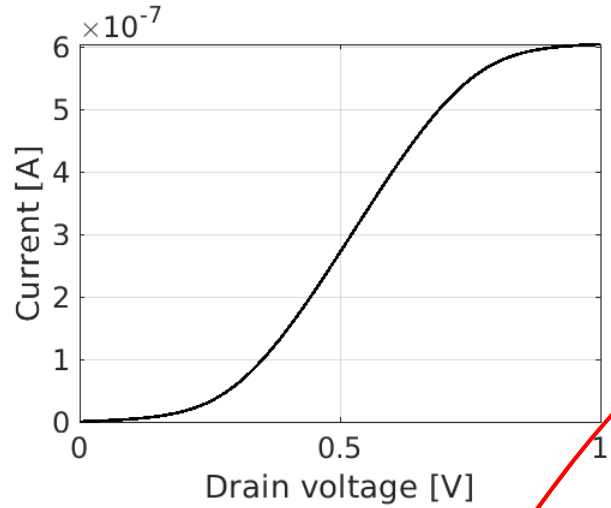
$$I = \frac{q}{\hbar} \frac{\gamma_1 \gamma_2}{\gamma_1 + \gamma_2} \int_{-\infty}^{\infty} [f_1(E + U) - f_2(E + U)] D(E) dE. \quad (4)$$

(b)

For the provided constants, the plots of the number of channel electrons and the channel current follow:



(a) Plot of channel electrons vs. drain voltage.



(b) Plot of channel current vs. drain voltage.

Figure 1: Number of electrons and current versus drain voltage.

Below is our code. Note that some variable names are different from those in the example code.

```
1
2 clear all;
3
4 %% Constants
5
6 % Physical constants
```

```

7  hbar = 1.052e-34;
8
9  % Single-charge coupling energy (eV)
10 U_0 = 0.25;
11 % (eV)
12 kBT = 0.025;
13 % Contact coupling coefficients (eV)
14 gamma_1 = 0.005;
15 gamma_2 = gamma_1;
16 gamma_sum = gamma_1 + gamma_2;
17 % Capacitive gate coefficient
18 a_G = 0.5;
19 % Capacitive drain coefficient
20 a_D = 0.5;
21 a_S = 1 - a_G - a_D;
22
23 % Central energy level
24 mu = 0;
25
26 % Energy grid, from -1eV to 1eV
27 NE = 501;
28 E = linspace(-1, 1, NE);
29 dE = E(2) - E(1);
30 % TODO name this better
31 cal_E = 0.2;
32
33 % Lorentzian density of states, normalized so the integral is 1
34 D = (gamma_sum / (2*pi)) ./ ( (E-cal_E).^2 + (gamma_sum/2).^2 );
35 D = D ./ (dE*sum(D));
36
37 % Reference no. of electrons in channel
38 N_0 = 0;
39
40 voltages = linspace(0, 1, 101);
41
42 % Terminal Voltages
43 V_G = 0;
44 V_S = 0;
45
46 for n = 1:length(voltages)
47     % Set varying drain voltage
48     V_D = voltages(n);
49
50     % Shifted energy levels of the contacts
51     mu_1 = mu - V_S;
52     mu_2 = mu - V_D;
53
54     % Laplace potential, does not change as solution is found (eV)
55     % q is factored out here, we are working in eV
56     U_L = - (a_G*V_G) - (a_D*V_D) - (a_S*V_S);
57
58     % Poisson potential must change, assume 0 initially (eV)
59     U_P = 0;
60
61     % Assume large rate of change
62     dU_P = 1;
63

```

```

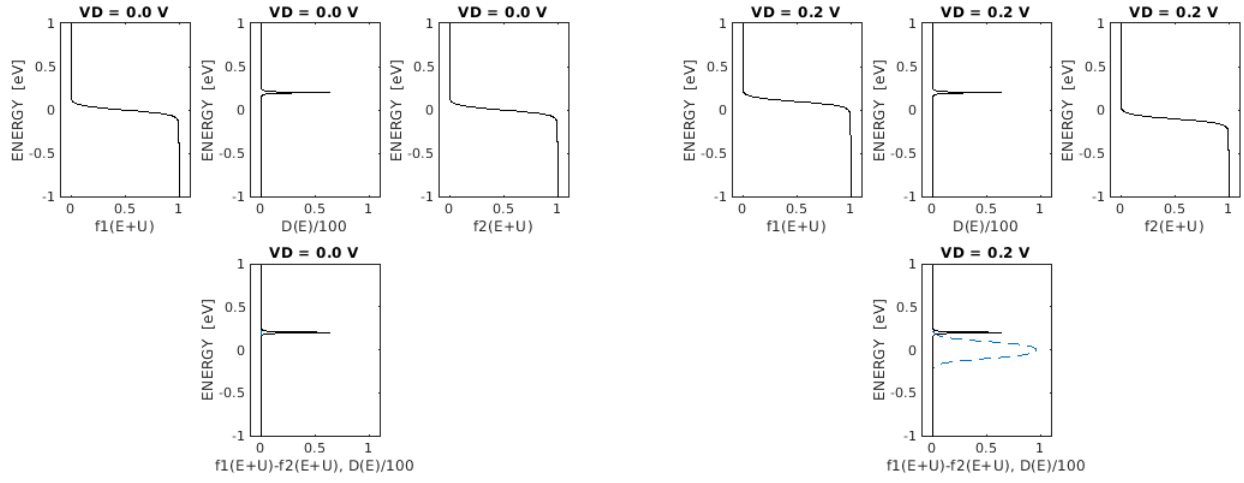
64 % Run until we get close enough to the answer
65 while dUP > 1e-6
66     % source Fermi function
67     f_1 = 1 ./ (1 + exp((E + UL + UP - mu_1) ./ kBT));
68     % drain Fermi function
69     f_2 = 1 ./ (1 + exp((E + UL + UP - mu_2) ./ kBT));
70
71     % Update channel electrons against potential
72     N(n) = dE * sum( ((gamma_1/gamma_sum) .* f_1 + (gamma_2/gamma_sum)
73         .* f_2) .* D);
74
75     % Re-update Poisson portion of potential
76     tmpUP = U_0 * ( N(n) - N_0);
77     dUP = abs(UP - tmpUP);
78
79     % Unsure why UP is updated incrementally, perhaps to avoid
80     % oscillations?
81     %UP = tmpUP;
82     %UP = UP + 0.1 * (tmpUP - UP);
83 end
84
85 % Calculate current based on solved potential.
86 % Note: f1 is dependent on changes in U but has been updated prior in
87 % the loop
88 I(n) = q * (q/hbar) * (gamma_1 * gamma_1 / gamma_sum) * dE * sum((f_1 -
89     f_2).*D);
90
91 end
92
93 %%Plotting commands
94
95 figure(1);
96 h = plot(voltages, N, 'k');
97 grid on;
98 set(h, 'linewidth', [2.0]);
99 set(gca, 'FontSize', [18]);
100 xlabel('Drain voltage [V]');
101 ylabel('Number of electrons');
102
103 figure(2);
104 h = plot(voltages, I, 'k');
105 grid on;
106 set(h, 'linewidth', [2.0]);
107 set(gca, 'FontSize', [18]);
108 xlabel('Drain voltage [V]');
109 ylabel('Current [A]');

```

(c)

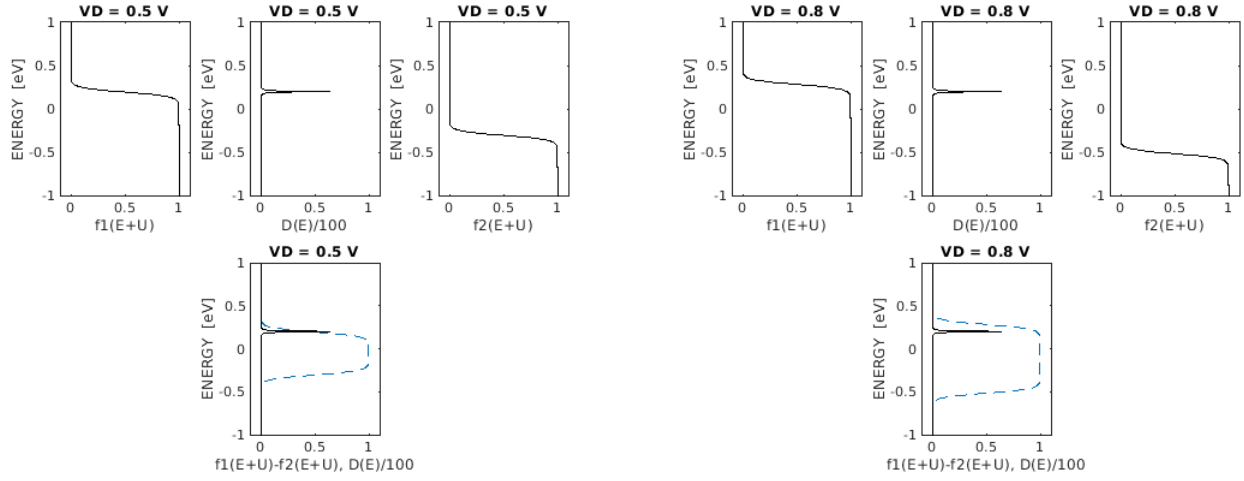
Code for this section can be found in appendix A.

(i)



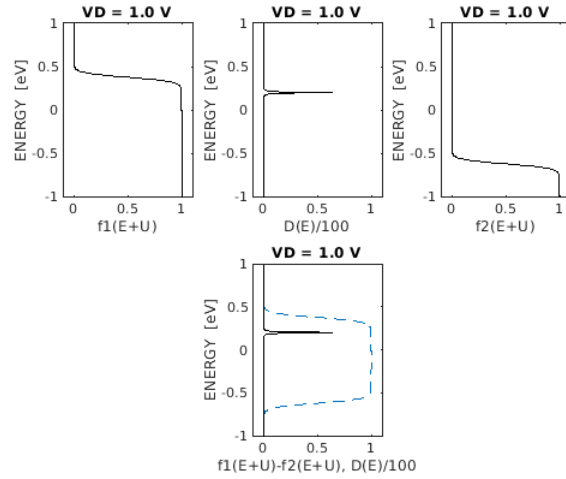
(a) Plot of channel electrons vs. drain voltage.

(b) Plot of channel electrons vs. drain voltage.



(c) Plot of channel electrons vs. drain voltage.

(d) Plot of channel electrons vs. drain voltage.



(e) Plot of channel electrons vs. drain voltage.

Figure 2: Visual representation of the Fermi functions of the contacts and channel.

Table 1 shows the variation in the difference between f_1 and f_2 at $E = \varepsilon$, and I at different drain voltages. We compare the differences between values at $V_D = 1.0 \text{ V}$ and $V_D = 0.8 \text{ V}$:

$$\frac{([f_1(E+U) - f_2(E+U)]|_{E=\varepsilon})|_{V_D=1.0 \text{ V}}}{([f_1(E+U) - f_2(E+U)]|_{E=\varepsilon})|_{V_D=0.8 \text{ V}}} = 1.0363,$$

$$\frac{I|_{V_D=1.0 \text{ V}}}{I|_{V_D=0.8 \text{ V}}} = 1.0504,$$

and between values at $V_D = 0.8 \text{ V}$ and $V_D = 0.5 \text{ V}$:

$$\frac{([f_1(E+U) - f_2(E+U)]|_{E=\varepsilon})|_{V_D=0.8 \text{ V}}}{([f_1(E+U) - f_2(E+U)]|_{E=\varepsilon})|_{V_D=0.5 \text{ V}}} = 2.1909,$$

$$\frac{I|_{V_D=0.8 \text{ V}}}{I|_{V_D=0.5 \text{ V}}} = 2.1218.$$

In both comparisons we see that I changes in proportion to $[f_1(E+U) - f_2(E+U)]|_{E=\varepsilon}$, as predicted by Equation (9).

V_D [V]	$[f_1(E+U) - f_2(E+U)] _{E=\varepsilon}$	I [nA]
0.0	0.000	0.0
0.2	0.015	17.0
0.5	0.440	271
0.8	0.964	575
1.0	0.999	604

Table 1: Differences in contact Fermi functions evaluated at $E = \varepsilon$ and current I at different drain voltages V_D . Values are taken from Figures 1b and 2a to 2e.

(ii)

Figure 3 has the Fermi functions marked at their "step points", or when they are equal to 0.5. This can be used to find the self-consistent potential U , via the equation for the source Fermi function:

$$f(E+U) = \frac{1}{1 + e^{(E+U-\mu_1)/k_B T}}$$

We could also use the drain Fermi function but since $V_S = 0$, it is simpler to use the source. The function will "step" when $E = \mu_1 - U$, which from Figure 3 occurs at $E = \mu_1 - U = 0.4$ for the source contact. Since $\mu_1 = \mu - qV_S = 0$ We can simply rearrange to find $U = -E = -0.4 \text{ eV}$.

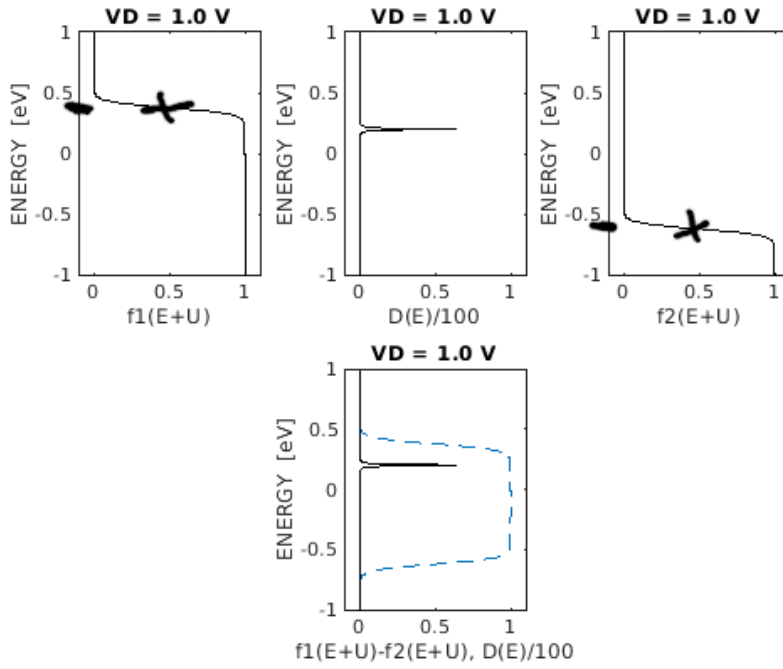


Figure 3: Marked step points of contact Fermi functions.

(iii)

At $V_D = 1V$, the source is trying to *fill* the channel level while the drain is trying to *empty* it. This is because the source has electrons at the channel level, and is filling these in while the drain does not have any and is attempting to bring the channel level back down to where it is.

(iv)

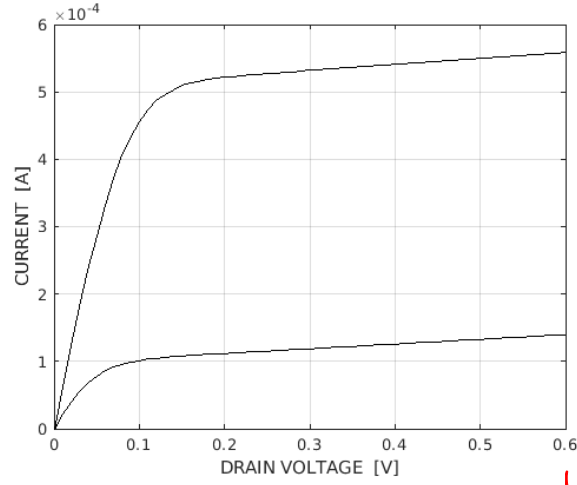
Referring to figure 3 again, we can see the areas where the difference between the Fermi functions of each contact are 1. Roughly, this means that the channel current I would remain the same if the channel energy level was anywhere between $0.3eV$ and $-0.5eV$.

(v)

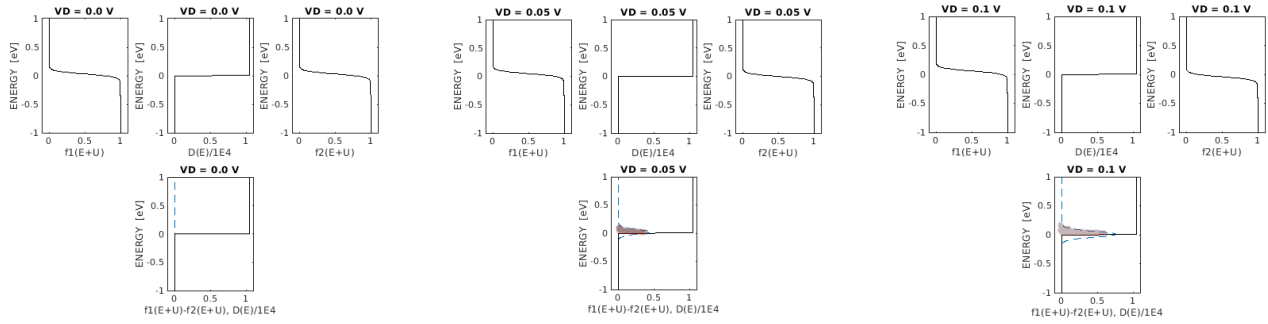
There is no current when $V_D = 0$ because the source does not want to fill the channel. It has no electrons at the channel energy level, and thus there is no impetus to fill the channel. A similar story occurs with the drain, in that it has no electrons at the appropriate energy level, and there are none in the channel for it to pull out.

Question 2

(a)



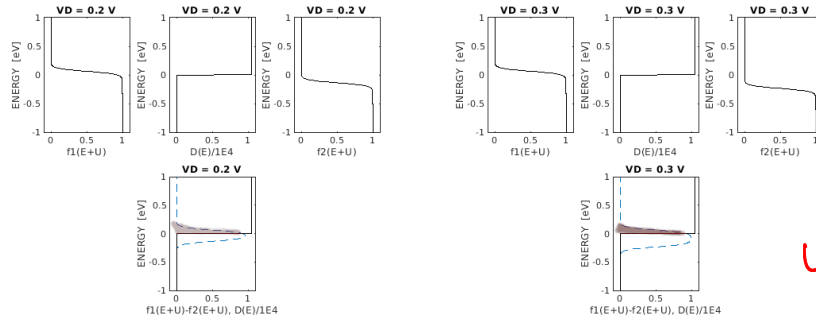
(a) I-V curves.



(b) Fermi functions at 0V.

(c) Fermi functions at 0.05V.

(d) Fermi functions at 0.1V.



(e) Fermi functions at 0.2V.

(f) Fermi functions at 0.3V.

Figure 4: (a) depicts I-V curves at $V_G = 0.5$ V (higher curve) and $V_G = 0.25$ V. (b) through (f) show Fermi functions and $D(E)$ at various drain voltages.

(b)

As the drain voltage increases, we see that the overlapping area under the "curve" of $f_1(E+U) - f_2(E+U)$ and $D(E)$ increases, up until the point where the drain only has electrons below the energy levels available in the channel. The difference function also reaches its maximum height and it widens downward rather than upward. At this point, the overlapping area no longer increases, and therefore the current does not increase either, hitting *saturation current*.

(c)

At $V_D = 0.3V$, the energy levels from approximately 0 to 0.2 eV are being used for electron transport. This is the range where the difference in the contact Fermi functions is more than 0 and the energy is more than 0. The difference between the two contacts is the greatest at 0eV, because this is the point at which their Fermi functions have the greatest difference, and thus will be making the most "effort" to equalize the channel potential.

(d)

Based on the supposed material changes, we would choose material A to maximize the drain current. The energy levels vanishing at $-0.4eV$ would mean that there is a greater number of energy levels that would be able to be used for conduction. There would be a larger *area* where there is a non-zero difference in the two Fermi functions at the contacts and there are energy levels available in the channel.

This can be contrasted with material B, which would have *no* energy levels in this "conduction" zone and thus no current would be able to flow at all.

Question 3

(a)

Below is our code. Note that some variable names are different from those in the example code.

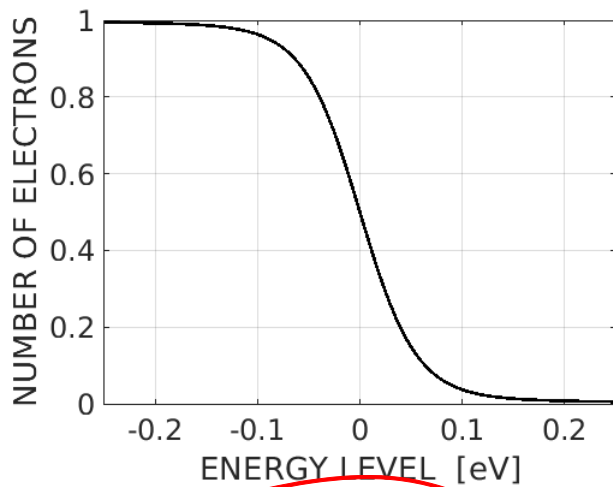
```
1 % Thermo-electric current
2
3 % Physical constants
4 hbar = 1.054e-34;
5 q = 1.602e-19;
6
7 % Parameters (eV)
8 kBT_1 = 0.025;
9 kBT_2 = 0.026;
10 mu = 0;
11 gamma_1 = 0.005;
12 gamma_2 = gamma_1;
13 gamma_sum = gamma_1 + gamma_2;
14
15 % Channel energy levels, varying between -0.25eV and 0.25eV
16 epsilon = linspace(-0.25, 0.25, 101);
17 depsilon = epsilon(2) - epsilon(1);
18
19 % Energy grid
20 E = linspace(-1, 1, 501);
21 dE = E(2) - E(1);
22
23 % Contact fermi functions
24 f_1 = 1 ./ (1 + exp((E - mu)./kBT_1));
25 f_2 = 1 ./ (1 + exp((E - mu)./kBT_2));
26
27 % Iterate through channel energy levels
28 for n = 1:length(epsilon)
29     % Compute energy level density functions - integral normalized to unity
30     D = (gamma_sum./(2*pi))./((E-epsilon(n)).^2+((gamma_sum./2).^2));
31     D = D./(dE*sum(D));
32
33     % Compute number of channel electrons
34
35     N(n) = dE*sum( ((gamma_1./gamma_sum).*f_1 + (gamma_2./gamma_sum).*f_2)
36         .*D );
```

```

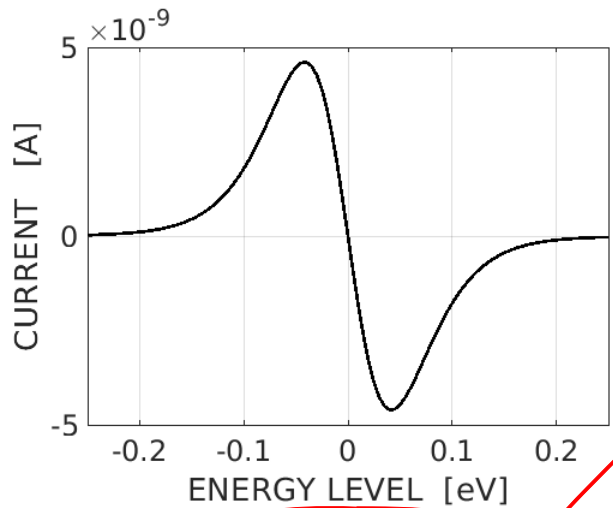
36
37 % Compute the current in Amps; factor of q to resolve units
38
39 I(n) = q*(q/hbar)*dE*sum((f_1 - f_2).*D.*gamma_1.*gamma_2./gamma_sum);
40
41 %plot f_1 - f_2 and D/2
42
43 if (abs(epsilon(n) + 0.05) <= depsilon / 2) & (epsilon(n) <= 0)
44     figure(3);
45     h = plot(f_1-f_2, E, 'x', D/2500, E, 'k-');
46     set(gca, 'FontSize', [18]);
47     axis([-0.01 0.02 -1 1]);
48     xlabel('f1(E) - f2(E), D(E)/2500');
49     ylabel('ENERGY [eV]');
50     legend('f1-f2', 'D(E)/2500');
51     title('CHANNEL LEVEL = -0.05 eV');
52 elseif (abs(epsilon(n)) <= depsilon / 2) & (epsilon(n) <= 0)
53     figure(4);
54     h = plot(f_1-f_2, E, 'x', D/2500, E, 'k-');
55     set(gca, 'FontSize', [18]);
56     axis([-0.01 0.02 -1 1]);
57     xlabel('f1(E) - f2(E), D(E)/2500');
58     ylabel('ENERGY [eV]');
59     legend('f1-f2', 'D(E)/2500');
60     title('CHANNEL LEVEL = 0 eV');
61 end
62
63 end
64
65 % Final plots
66 figure(1);
67

```

(b)

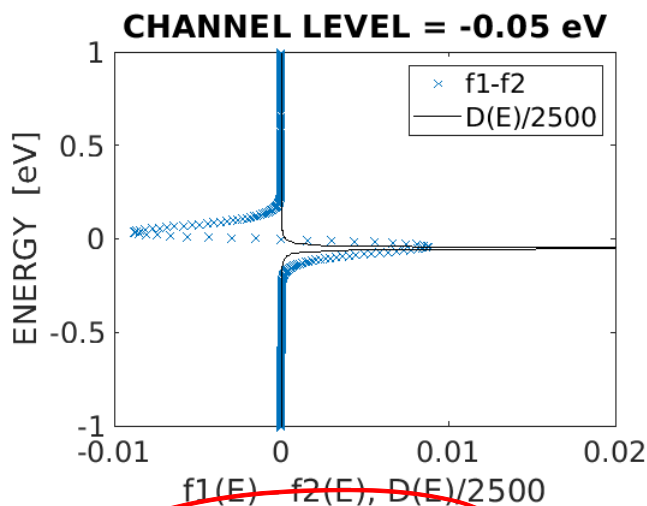


(a) Fermi Functions at 0.3V.

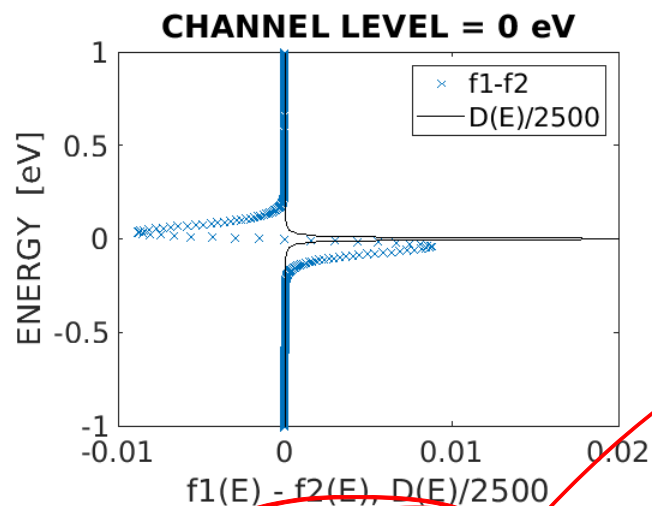


(b) Fermi Functions at 0.3V.

(c)



(a) Fermi Functions at 0.3V.



(b) Fermi Functions at 0.3V.

(d)

The difference in temperature causes a difference in the sharpness of the contact Fermi functions. This in turn leads to the behaviour in $f_1 - f_2$ seen in Figures 6a and 6b. As seen in the previous questions, the current is proportional to the area under the curve of the $D(E) * [f_1 - f_2]$. When the channel level is $\varepsilon = -0.05$ eV, the positive region of $[f_1 - f_2]$ overlaps the non-zero part of $D(E)$, giving a positive current. Alternatively, when $\varepsilon = 0$ eV, half of the area under $D(E)$ overlaps with the negative part of $[f_1 - f_2]$, while half overlaps the positive part. Thus the areas cancel out completely, and the resultant current is 0. A plot of $\varepsilon = +0.05$ eV would show overlap of $D(E)$ with the negative part of $[f_1 - f_2]$, explaining why we get a reverse current flow at that channel level. The maximum current occurs at $\varepsilon = \pm 0.4$ eV (relative to μ).

Question 4

(a)

(i)

$$I = 0, N = 0$$

This is because the only allowed energy level in the channel is at a higher energy level than exists in either of the contacts, thus there are no electrons that would flow into the channel from either contact, thus no current *and* no electrons in the channel.

(ii)

$$I = 608 \text{ nA}, N = 0.5$$

Given that we are operating with a single energy level in the channel, we can use the equations 9 and 10 (provided in the assignment) directly.

$$I = \frac{q}{h} \cdot \frac{0.005 \text{ eV} \cdot 0.005 \text{ eV}}{0.005 \text{ eV} + 0.005 \text{ eV}} \cdot [1 - 0] = 608 \text{ nA}$$

$$N = \frac{0.005 \text{ eV} \cdot 1 + 0.005 \text{ eV} \cdot 0}{0.005 \text{ eV} + 0.005 \text{ eV}} = 0.5$$

(iii)

$$I = 0 \text{ A}, N = 1$$

Given that we are operating with a single energy level in the channel, we can use the equations 9 and 10 (provided in the assignment) directly.

$$I = \frac{q}{h} \cdot \frac{0.005\text{eV} \cdot 0.005\text{eV}}{0.005\text{eV} + 0.005\text{eV}} \cdot [1 - 1] = 0 \text{ A}$$

$$N = \frac{0.005\text{eV} \cdot 1 + 0.005\text{eV} \cdot 1}{0.005\text{eV} + 0.005\text{eV}} = 1$$

(b)

(i)

For $f_1(E + U)$ the step point occurs at $E = \mu_1 - U = 0.25 \text{ eV}$. Since $U = -0.25 \text{ eV}$, it follows that $\mu_1 = 0 \text{ eV}$. Since $\mu_1 = \mu - qV_S$ and $\mu = 0 \text{ eV}$, $V_S = 0 \text{ V}$. For $f_2(E + U)$ the step point occurs at $E = \mu_2 - U = -0.25 \text{ eV}$. Since $U = -0.25 \text{ eV}$, it follows that $\mu_2 = -0.5 \text{ eV}$. Since $\mu_1 = \mu - qV_D$ and $\mu = 0 \text{ eV}$, $V_D = 0.5 \text{ V}$.

(ii)

For $f_1(E)$ the step point occurs at $E = \mu_1 = 0.25 \text{ eV}$. Since $\mu_1 = \mu - qV_S$ and $\mu = 0 \text{ eV}$, $V_S = -0.25 \text{ V}$. For $f_2(E)$ the step point occurs at $E = \mu_2 = -0.25 \text{ eV}$. Since $\mu_1 = \mu - qV_D$ and $\mu = 0 \text{ eV}$, $V_D = 0.25 \text{ V}$. This assumes $U = 0 \text{ eV}$.

(c)

(i)

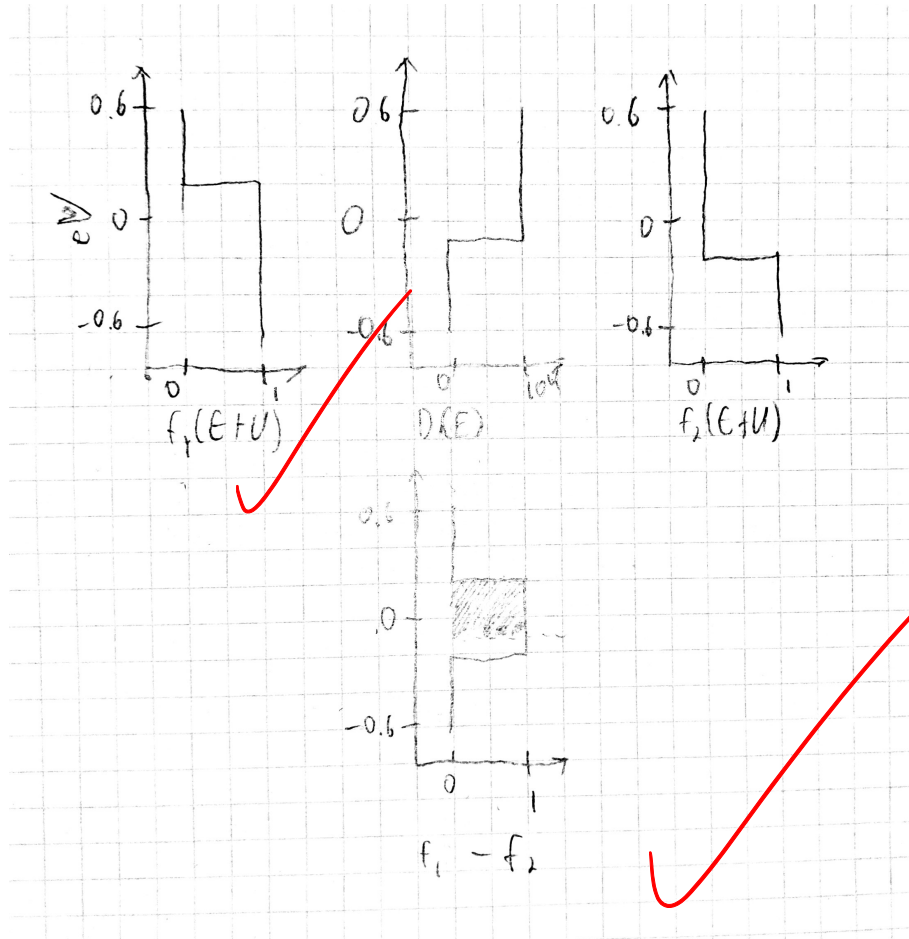


Figure 7: Visualisation of energy levels.

(ii)

Starting with equation 2 in the assignment we get:

$$I = \frac{q}{h} \cdot \frac{0.005^2}{0.01} \cdot \int_{-0.1}^{0.2} [1 - 0] \cdot 10^4 dE$$
$$I = \frac{q}{h} \cdot \frac{0.005^2}{0.01} \cdot [10^4 \cdot 0.2 - 10^4 \cdot -0.1]$$
$$I = 1.8 \text{ mA}$$

(iii)

The graph for the fermi functions at the saturation potentials will look much the same, except that they will be shifted up. This means that there is more area "under" the difference between the fermi functions and thus the bounds of integration can shift and become $[-0.1, 0.3]$.

$$I = \frac{q}{h} \cdot \frac{0.005^2}{0.01} \cdot \int_{-0.1}^{0.3} [1 - 0] \cdot 10^4 dE$$
$$I = \frac{q}{h} \cdot \frac{0.005^2}{0.01} \cdot [10^4 \cdot 0.3 - 10^4 \cdot -0.1]$$
$$I = 2.4 \text{ mA}$$

(d)

Using equation (5) in the assignment and plugging in the given values we obtain:

$$U = -q \left[\frac{C_S V_S + C_G V_G + C_D V_D}{C_E} \right] + \frac{q^2 (N - N_0)}{C_E}$$
$$U = -\alpha_S V_S - \alpha_G V_G - \alpha_D V_D + U_0 (N - N_0) \text{ eV}$$
$$U = -0 \cdot 0 - 0.5 \cdot 0 \text{ eV} - 0.5 \cdot 0.6 \text{ eV} + 0.25 \text{ eV} \cdot (0.325 - 0) \text{ eV}$$
$$U = -0.21875 \text{ eV}$$

Then, starting with Equation 3 and plugging in $D(E - U) = \delta(E - \varepsilon)$, we obtain

$$N = \frac{\gamma_1 f_1(\varepsilon + U) + \gamma_2 f_2(\varepsilon + U)}{\gamma_1 + \gamma_2}$$

Recalling that the expressions for the contact Fermi functions are (with $\mu = 0 \text{ eV}$):

$$f_1(\varepsilon + U) = \frac{1}{1 + e^{(\varepsilon + U + qV_S)/k_B T}} = \frac{1}{1 + e^{(0.2 - 0.21875 + 0)/0.025}} = 0.679$$
$$f_2(\varepsilon + U) = \frac{1}{1 + e^{(\varepsilon + U + qV_D)/k_B T}} = \frac{1}{1 + e^{(0.2 - 0.21875 + 0.6)/0.025}} \simeq 0$$

Then, solving for γ_2 :

$$\gamma_2 = \gamma_2 \frac{N - f_1(\varepsilon + U)}{f_2(\varepsilon + U) - N} = 5.45 \times 10^{-3} \text{ eV}$$

(e)

Assuming the density of states for each molecule can be modeled by $D(E) = \delta(E - \varepsilon)$, Equation (12) in the assignment is valid here. Thus the current will be maximized when $[f_1(E) - f_2(E)]|_{E=\varepsilon}$ is maximized. Solving $[f_1(E) - f_2(E)]|_{E=\varepsilon}$ for each molecule, we obtain:

Molecule A:

$$[f_1(E) - f_2(E)]|_{E=\varepsilon_A} = \frac{1}{1 + e^{\frac{\varepsilon_A}{k_B T_1}}} - \frac{1}{1 + e^{\frac{\varepsilon_A}{k_B T_2}}} = \frac{1}{1 + e^{\frac{0}{0.024}}} - \frac{1}{1 + e^{\frac{0}{0.027}}} = 0$$

Molecule B:

$$[f_1(E) - f_2(E)]|_{E=\varepsilon_B} = \frac{1}{1 + e^{\frac{\varepsilon_B}{k_B T_1}}} - \frac{1}{1 + e^{\frac{\varepsilon_B}{k_B T_2}}} = \frac{1}{1 + e^{\frac{-0.05}{0.024}}} - \frac{1}{1 + e^{\frac{-0.05}{0.027}}} = 0.02493$$

Molecule C:

$$[f_1(E) - f_2(E)]|_{E=\varepsilon_C} = \frac{1}{1 + e^{\frac{\varepsilon_C}{k_B T_1}}} - \frac{1}{1 + e^{\frac{\varepsilon_C}{k_B T_2}}} = \frac{1}{1 + e^{\frac{-0.1}{0.024}}} - \frac{1}{1 + e^{\frac{-0.1}{0.027}}} = 0.00877$$

Molecule B should be chosen.

(f)

Referring again to equation 2 in the assignment, we know that $D(E)$ is valid for all E , however since γ_1 is dependant on the energy level, we can use it to reduce our limits. For material A, this means we only care about E above $0eV$, and for B, E below $0eV$. Since we know the voltages on the contacts, we can calculate the effective fermi level at each.

$$\mu_1 = \mu_0 - V_S = 0 - (-2V) = 2 eV$$

$$\mu_2 = \mu_0 - V_D = 0 - 1V = -1 eV$$

With the fermi levels of each contact, we can adjust the limits of integration further for each material. Material A can be evaluated on $[0eV, 2eV]$, and material B can be evaluated on $[-1eV, 0eV]$.

$$I_A = \frac{q}{\hbar} \cdot \frac{0.005^2}{0.01} \cdot \int_0^2 [1 - 0] \cdot 10^4 dE$$

$$I_A = 12.2 mA$$

$$I_B = \frac{q}{\hbar} \cdot \frac{0.005^2}{0.01} \cdot \int_0^2 [1 - 0] \cdot 10^4 dE$$

$$I_A = 6.1 mA$$

Material A should be chosen.

(g)

Using Ohm's law we find the corresponding conductance:

$$\sigma_{max} = \frac{I_{max}}{V} = \frac{500 nA}{4.3 mV} = 116 \mu S.$$

We expect this result to be an integer multiple of $G_0 = 38.76 \mu S$, the quantum of conductance. We find

$$\frac{\sigma_{max}}{G_0} = 3.$$

We conclude there are 3 levels.

A Question 1b Code

```
1 clear all;
2
3 %% Constants
4
5 % Physical constants
6 hbar = 1.052e-34;
7 q = 1.602e-19;
8 %epsilon_0 = 8.854e-12;
9 %epsilon_r = 4;
10 %mstar = 0.25 * 9.11e-31;
11
12 % Single-charge coupling energy (eV)
13 U_0 = 0.25;
14 % (eV)
15 kBT = 0.025;
16 % Contact coupling coefficients (eV)
17 gamma_1 = 0.005;
18 gamma_2 = gamma_1;
19 gamma_sum = gamma_1 + gamma_2;
20 % Capacitive gate coefficient
21 a_G = 0.5;
22 % Capacitive drain coefficient
23 a_D = 0.5;
24 a_S = 1 - a_G - a_D;
25
26 % Central energy level
27 mu = 0;
28
29 % Energy grid, from -1eV to 1eV
30 NE = 501;
31 E = linspace(-1, 1, NE);
32 dE = E(2) - E(1);
33 % TODO name this better
34 cal_E = 0.2;
35
36 % Lorentzian density of states, normalized so the integral is 1
37 D = (gamma_sum / (2*pi)) ./ ( (E-cal_E).^2 + (gamma_sum/2).^2 );
38 D = D ./ (dE*sum(D));
39
40 % Reference no. of electrons in channel
41 N_0 = 0;
42
43 voltages = linspace(0, 1, 101);
44 dV = voltages(2) - voltages(1);
45
46 % Terminal Voltages
47 V_G = 0;
48 V_S = 0;
49
50 for n = 1:length(voltages)
51     % Set varying drain voltage
52     V_D = voltages(n);
53
54     % Shifted energy levels of the contacts
55     mu_1 = mu - V_S;
```

```

56 mu_2 = mu - V_D;
57
58 % Laplace potential, does not change as solution is found (eV)
59 % q is factored out here, we are working in eV
60 U_L = - (a_G*V_G) - (a_D*V_D) - (a_S*V_S);
61
62 % Poisson potential must change, assume 0 initially (eV)
63 U_P = 0;
64
65 % Assume large rate of change
66 dU_P = 1;
67
68 % Run until we get close enough to the answer
69 while dU_P > 1e-6
70     % source Fermi function
71     f_1 = 1 ./ (1 + exp((E + U_L + U_P - mu_1) ./ kBT));
72     % drain Fermi function
73     f_2 = 1 ./ (1 + exp((E + U_L + U_P - mu_2) ./ kBT));
74
75     % Update channel electrons against potential
76     N(n) = dE * sum( ((gamma_1/gamma_sum) .* f_1 + (gamma_2/gamma_sum)
77         .* f_2) .* D);
78
79     % Re-update Poisson portion of potential
80     tmpU_P = U_0 * ( N(n) - N_0);
81     dU_P = abs(U_P - tmpU_P);
82
83     % Unsure why U_P is updated incrementally, perhaps to avoid
84     % oscillations?
85     %U_P = tmpU_P;
86     U_P = U_P + 0.1 * (tmpU_P - U_P);
87 end
88
89 % Calculate current based on solved potential.
90 % Note: f1 is dependent on changes in U but has been updated prior in
91 % the loop
92 I(n) = q * (q/hbar) * (gamma_1 * gamma_1 / gamma_sum) * dE * sum((f_1 -
93     f_2).*D);
94
95 if (abs(V_D-0.0) <= dV/2)
96     figure(3); title('VD = 0.0 V');
97     subplot(2,3,1); plot(f_1,E,'k-'); axis([-0.1 1.1 -1 1]);
98     xlabel('f1(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.0 V');
99     subplot(2,3,2); plot(D/100,E,'k-'); axis([-0.1 1.1 -1 1]);
100    xlabel('D(E)/100'); ylabel('ENERGY [eV]'); title('VD = 0.0 V');
101    subplot(2,3,3); plot(f_2,E,'k-'); axis([-0.1 1.1 -1 1]);
102    xlabel('f2(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.0 V');
103    subplot(2,3,5); plot(f_1-f_2,E,'-',D/100,E,'k-'); axis([-0.1 1.1
104        -1 1]);
105    xlabel('f1(E+U)-f2(E+U), D(E)/100'); ylabel('ENERGY [eV]'); title(
106        'VD = 0.0 V');
107 elseif (abs(V_D-0.2) <= dV/2)
108     figure(4); title('VD = 0.2 V');
109     subplot(2,3,1); plot(f_1,E,'k-'); axis([-0.1 1.1 -1 1]);
110     xlabel('f1(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.2 V');
111     subplot(2,3,2); plot(D/100,E,'k-'); axis([-0.1 1.1 -1 1]);
112     xlabel('D(E)/100'); ylabel('ENERGY [eV]'); title('VD = 0.2 V');

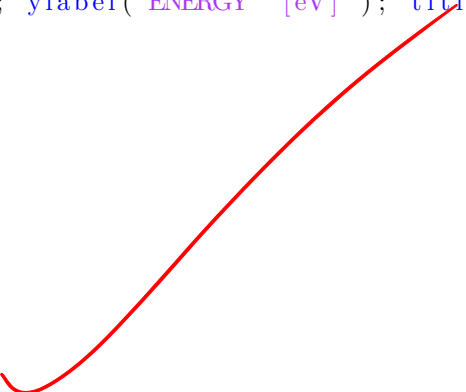
```



```

107     subplot(2,3,3); plot(f_2,E,'k-'); axis([-0.1 1.1 -1 1]);
108     xlabel('f2(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.2 V');
109     subplot(2,3,5); plot(f_1-f_2,E,'--',D/100,E,'k-'); axis([-0.1 1.1
110         -1 1]);
111     xlabel('f1(E+U)-f2(E+U), D(E)/100'); ylabel('ENERGY [eV]'); title(
112         'VD = 0.2 V');
113     elseif (abs(VD-0.5) <= dV/2)
114         figure(5); title('VD = 0.5 V');
115         subplot(2,3,1); plot(f_1,E,'k-'); axis([-0.1 1.1 -1 1]);
116         xlabel('f1(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.5 V');
117         subplot(2,3,2); plot(D/100,E,'k-'); axis([-0.1 1.1 -1 1]);
118         xlabel('D(E)/100'); ylabel('ENERGY [eV]'); title('VD = 0.5 V');
119         subplot(2,3,3); plot(f_2,E,'k-'); axis([-0.1 1.1 -1 1]);
120         xlabel('f2(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.5 V');
121         subplot(2,3,5); plot(f_1-f_2,E,'--',D/100,E,'k-'); axis([-0.1 1.1
122             -1 1]);
123         xlabel('f1(E+U)-f2(E+U), D(E)/100'); ylabel('ENERGY [eV]'); title(
124             'VD = 0.5 V');
125     elseif (abs(VD-0.8) <= dV/2)
126         figure(6); title('VD = 0.8 V');
127         subplot(2,3,1); plot(f_1,E,'k-'); axis([-0.1 1.1 -1 1]);
128         xlabel('f1(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.8 V');
129         subplot(2,3,2); plot(D/100,E,'k-'); axis([-0.1 1.1 -1 1]);
130         xlabel('D(E)/100'); ylabel('ENERGY [eV]'); title('VD = 0.8 V');
131         subplot(2,3,3); plot(f_2,E,'k-'); axis([-0.1 1.1 -1 1]);
132         xlabel('f2(E+U)'); ylabel('ENERGY [eV]'); title('VD = 0.8 V');
133         subplot(2,3,5); plot(f_1-f_2,E,'--',D/100,E,'k-'); axis([-0.1 1.1
134             -1 1]);
135         xlabel('f1(E+U)-f2(E+U), D(E)/100'); ylabel('ENERGY [eV]'); title(
136             'VD = 0.8 V');
137     elseif (abs(VD-1.0) <= dV/2)
138         figure(7); title('VD = 1.0 V');
139         subplot(2,3,1); plot(f_1,E,'k-'); axis([-0.1 1.1 -1 1]);
140         xlabel('f1(E+U)'); ylabel('ENERGY [eV]'); title('VD = 1.0 V');
141         subplot(2,3,2); plot(D/100,E,'k-'); axis([-0.1 1.1 -1 1]);
142         xlabel('D(E)/100'); ylabel('ENERGY [eV]'); title('VD = 1.0 V');
143         subplot(2,3,3); plot(f_2,E,'k-'); axis([-0.1 1.1 -1 1]);
144         xlabel('f2(E+U)'); ylabel('ENERGY [eV]'); title('VD = 1.0 V');
145         subplot(2,3,5); plot(f_1-f_2,E,'--',D/100,E,'k-'); axis([-0.1 1.1
146             -1 1]);
147         xlabel('f1(E+U)-f2(E+U), D(E)/100'); ylabel('ENERGY [eV]'); title(
148             'VD = 1.0 V');
149     end
150 end
151
152 %%Plotting commands
153 figure(1);
154 h = plot(voltages, N, 'k');
155 grid on;
156 set(h, 'linewidth', [2.0]);
157 set(gca, 'FontSize', [18]);
158 xlabel('Drain voltage [V]');
159 ylabel('Number of electrons');
160

```



```
156 figure(2);
157 h = plot(voltages , I , 'k');
158 grid on;
159 set(h, 'linewidth' ,[2.0]);
160 set(gca, 'FontSize' ,[18]);
161 xlabel( 'Drain voltage [V] ');
162 ylabel( 'Current [A] ');
```